

**THE UNITED STATES PATENT AND TRADEMARK OFFICE**

In re Application of  
Jack A. Mandelman

Group Art:

Examiner:

Title: FIELD-SHIELD TRENCH ISOLATION  
FOR GIGABIT DRAMS

Serial No.:

Filed: February 5, 1999

Honorable Commissioner of Patents and Trademarks  
Washington, D.C. 20231

Sir:

Applicants respectfully request that the following references be considered in the examination of the above-identified application. A copy of each reference is enclosed.

**Cited Art**

U.S. Patent No. 5,557,135 (M. Haskimoto, issued September 17, 1996, and cited and discussed in the specification on page 5.


An article entitled "Effects Of A New Trench-isolated Transistor Using Sidewall Gates" by K. Hieda et al, IEEE Transactions On Elecron Devices, Vol. 36, No. 9, September 1989.

**REMARKS**

Under Rule 37 C.F.R. 1,98(a), which is effective as of March 16, 1992, applicants submit that no specific comments are necessary for any of the above cited English Language publications.

For the Examiner's convenience, applicants have attached a completed PTO-1449 form hereto.

Respectfully submitted,



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